

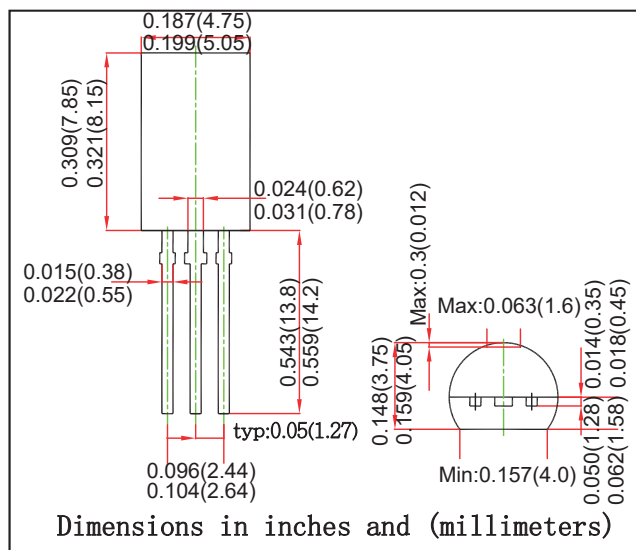
TO-92L Plastic-Encapsulate Transistors

FEATURES

- High Voltage: $V_{CEO}=160V$
- Large Continuous Collector Current Capability
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style:TO-92L molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	160	V
V_{CEO}	Collector-Emitter Voltage	160	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	1	A
P_C	Collector Power Dissipation	0.75	W
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55~+150	°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	160			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	160			V
Emitter-Base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=150V, I_E=0$			1	μA
Collector cut-off current	I_{CER}	$V_{CB}=150V, R_{EB}=10M\Omega$			10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6V, I_C=0$			1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=5V, I_C=200mA$	60		250	
	$h_{FE(2)}$	$V_{CE}=5V, I_C=10mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$			1	V
Base-emitter voltage	V_{BE}	$I_C=5mA, V_{CE}=5V$			0.75	V
Transition frequency	f_T	$V_{CE}=5V, I_C=200mA$	20			MHz

RATINGS AND CHARACTERISTIC CURVES

